

## SMALL SIGNAL NPN TRANSISTORS

#### **PRELIMINARY DATA**

Type	Marking
BC847B	1F
BC847C	1G

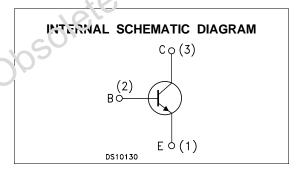
- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- MINIATURE SOT-23 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- BC847B THE PNP COMPLEMENTARY TYPE IS BC857B

#### **APPLICATIONS**

- WELL SUITABLE FOR PORTABLE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTORS WITH HIGH GAIN AND LOW SATURATION VOLTAGE

Product(s)





### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Усво	Collector-Base Voltage (I <sub>E</sub> = 0)	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)	45	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)	6	V
Ic	Collector Current	100	mA
I <sub>CM</sub>	Collector Peak Current	200	mA
P <sub>tot</sub>	Total Dissipation at T <sub>C</sub> = 25 °C	250	mW
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

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### THERMAL DATA

R <sub>thj-amb</sub> •	Thermal Resistance Junction-Ambient	Max	500	°C/W	
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<sup>•</sup> Device mounted on a PCB area of 1 cm<sup>2</sup>.

# **ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

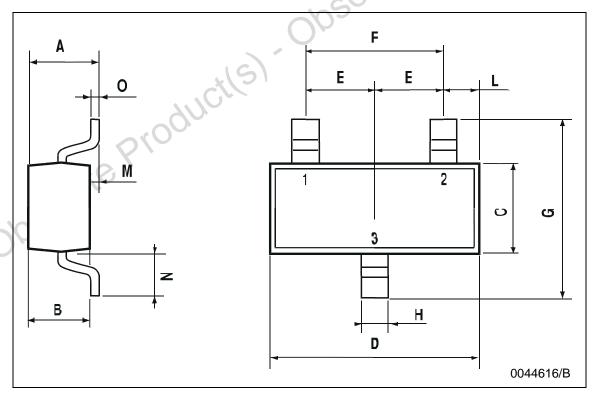
Symbol	Parameter	Test Conditions		Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 30 V V <sub>CB</sub> = 30 V			15 5	nΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			100	nA
V <sub>(BR)</sub> CBO	Collector-Base Breakdown Voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = 10 μA	50			V
V <sub>(BR)CEO*</sub>	Collector-Emitter Breakdown Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 2 mA	45			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 10 μA	6		Cil	V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	$\begin{split} I_C &= 10 \text{ mA} & I_B = 0.5 \text{ mA} \\ I_C &= 100 \text{ mA} & I_B = 5 \text{ mA} \end{split}$	~ <	0.09 0.2	0.25 0.6	V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	$\begin{split} I_C = 10 \text{ mA} & I_B = 0.5 \text{ mA} \\ I_C = 100 \text{ mA} & I_B = 5 \text{ mA} \end{split}$	. ( )	0.7 0.9		V V
V <sub>BE(on)</sub> *	Base-Emitter On Voltage	I <sub>C</sub> = 2 mA	0.58	0.66	0.7 0.77	V V
h <sub>FE</sub> *	DC Current Gain	$I_C = 10 \ \mu A$ for BC847B for BC847C $I_C = 2 \ mA$ for BC847B for BC847B for BC847C	200 420	150 270 290 520	450 800	
f <sub>T</sub>	Transition Frequency	$I_C = 10 \text{ mA} \text{ V}_{CE} = 5 \text{ V} \text{ f} = 100 \text{MHz}$	100			MHz
ССВО	Collector-Base Capacitance	$I_E = 0$ $V_{CB} = 10 \text{ V}$ $f = 1 \text{ MHz}$		2.5		pF
NF	Noise Figure	$\begin{aligned} &V_{CE} = 5 \; V  I_{C} = 0.2 \; mA  f = 1KHz \\ &\Delta f = 200 \; Hz  R_{G} = 2 \; K\Omega \end{aligned}$		2	10	dB

<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

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## **SOT-23 MECHANICAL DATA**

DIM.	mm		mils			
Dini.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	0.85		1.1	33.4		43.3
В	0.65		0.95	25.6		37.4
С	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
Н	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8	100/0	23.6
М	0		0.1	0	260	3.9
N	0.3		0.65	11.8		25.6
0	0.09		0.17	3.5		6.7



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